

IN THE CLAIMS

Please amend the claims to read as follows:

1. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
a flat-plate-shaped cavity made in the semiconductor substrate; and
an element isolating region formed in the surface of the semiconductor substrate and
located at the sides of the cavity, the cavity being wider than an element region provided on the cavity.
2. (Canceled)
3. (Currently Amended) The semiconductor device according to claim 1, wherein
the element isolating region and the cavity enclose the element region ~~provided at the top of the cavity~~ and electrically separate the element region from the semiconductor substrate.
4. (Currently Amended) The semiconductor device according to claim 1, wherein
only one element region is provided ~~at the top of~~ on the cavity.
5. (Currently Amended) The semiconductor device according to claim 1, wherein
~~the base of the element isolating region is less deep than the bottom of the cavity and deeper than~~
~~the top of the cavity~~ element region.

6. (Original) The semiconductor device according to claim 1, wherein the element isolating region is formed of an oxide film obtained by oxidizing the semiconductor substrate.

7. (Currently Amended) A semiconductor device comprising:
a semiconductor substrate;
a plurality of flat-plate-shaped cavities made in the semiconductor substrate; and
an element isolating region formed in the surface of the semiconductor substrate between adjacent ones of the cavities, a part of the element isolating region being exposed to ~~the sides of~~ the cavities, each cavity being wider than each element region provided on each cavity,
respectively.

8. (Canceled)

9. (Currently Amended) The semiconductor device according to claim 7, wherein the element isolating region and the cavities enclose the element regions ~~provided at the top of~~ the cavities and electrically separate the element regions from the semiconductor substrate.

10. (Currently Amended) The semiconductor device according to claim 7, wherein only one element region is provided ~~at the top of~~ on the cavity.

11. (Currently Amended) The semiconductor device according to claim 7, wherein the ~~base of the~~ element isolating region is less deep than the ~~bottom of the~~ cavities and deeper than the ~~top of the cavities~~ element region.

12. (Original) The semiconductor device according to claim 7, wherein the element isolating region is formed of an oxide film obtained by oxidizing the semiconductor substrate.

13-19. (Canceled)

20. (Currently Amended) A method of fabricating a semiconductor device, comprising:
making flat-plate-shaped cavities partly in a semiconductor substrate;
forming an insulating film in the surface of the semiconductor substrate between adjacent ones of the cavities in such a manner that a part of the insulating film is exposed to ~~the sides of~~ the cavities so as to electrically separate element regions provided ~~at the top of the adjacent~~ on the cavities from each other, each cavity being wider than each element region; and
forming semiconductor elements on the element regions.

21. (Original) The method according to claim 20, wherein the insulating film is formed by oxidizing the surface of the semiconductor substrate.

22. (Canceled)

23. (Original) The method according to claim 20, wherein the insulating film and the cavities enclose the element regions and electrically separate the element regions from the semiconductor substrate.

24. (Currently Amended) The method according to claim 20, wherein only one element region provided ~~at the top of~~ on each of the cavities.

25. (Currently Amended) The method according to claim 20, wherein the ~~base of the~~ insulating film is less deep than the ~~bottom of the~~ cavities and deeper than the ~~top of the cavities~~ element region.

26. (Canceled)

27. (New) The semiconductor device according to claim 1, wherein the cavity has no element therein.

28. (New) The semiconductor device according to claim 7, wherein the cavity has no element therein.

29. (New) The method according to claim 20, wherein the cavity has no element therein.